

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SB905

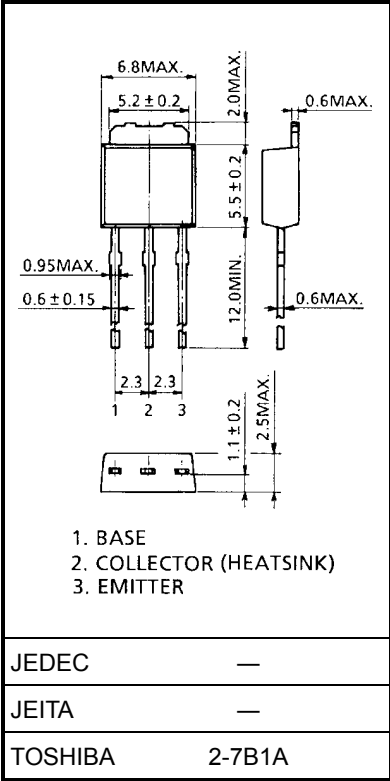
Power Amplifier Applications

- Complementary to SD1220

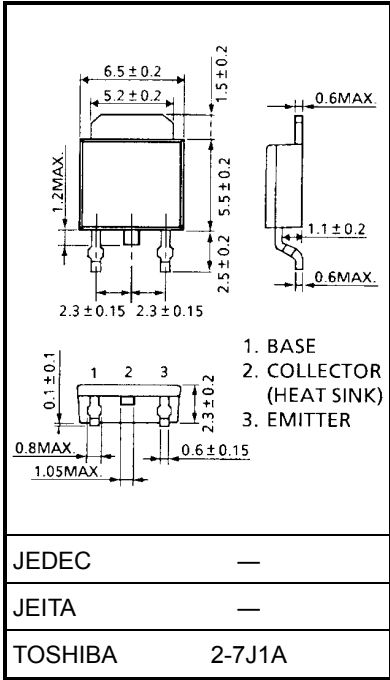
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V _{CBO}	-150	V
Collector-emitter voltage		V _{CEO}	-150	V
Emitter-base voltage		V _{EBO}	-6	V
Collector current		I _C	-1.5	A
Base current		I _B	-1.0	A
Collector power dissipation	Ta = 25°C	P _C	1.0	W
	Tc = 25°C		10	
Junction temperature		T _j	150	°C
Storage temperature range		T _{stg}	-55 to 150	°C

Unit: mm



Weight: 0.36 g (typ.)



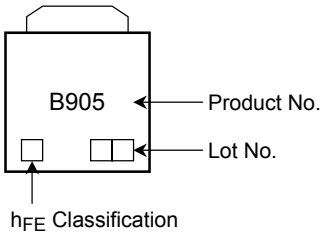
Weight: 0.36 g (typ.)

Electrical Characteristics (Ta = 25°C)

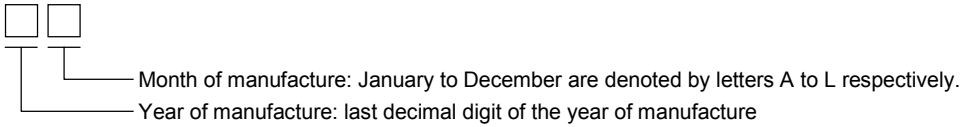
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	ICBO	V _{CB} = -150 V, I _E = 0	—	—	-1.0	μA
Emitter cut-off current	IEBO	V _{EB} = -6 V, I _C = 0	—	—	-1.0	μA
Collector-emitter breakdown voltage	V _(BR) CEO	I _C = -10 mA, I _B = 0	-150	—	—	V
DC current gain	h _{FE} (Note)	V _{CE} = -5 V, I _C = -200 mA	60	—	320	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = -500 mA, I _B = -50 mA	—	—	-1.5	V
Base-emitter voltage	V _{BE}	V _{CE} = -5 V, I _C = -5 mA	-0.5	—	-0.8	V
Transition frequency	f _T	V _{CE} = -5 V, I _C = -200 mA	15	50	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	—	—	35	pF

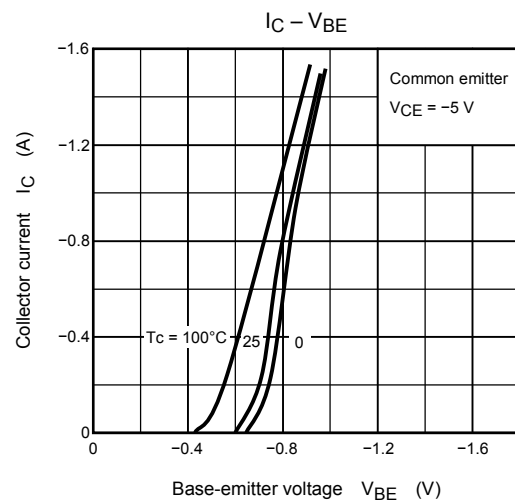
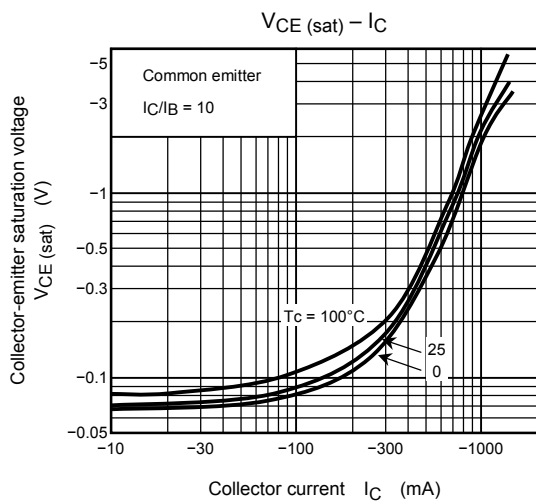
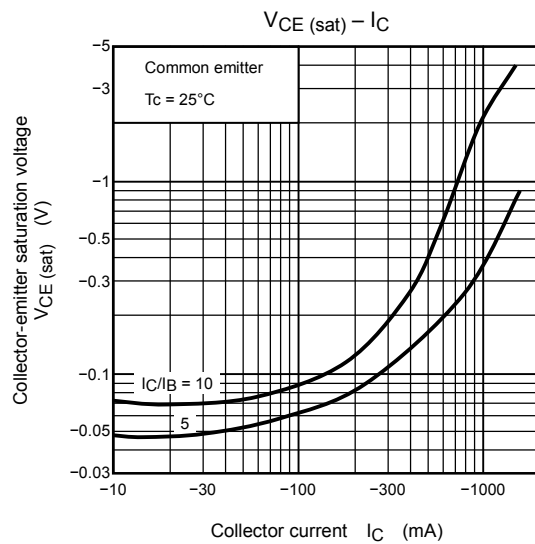
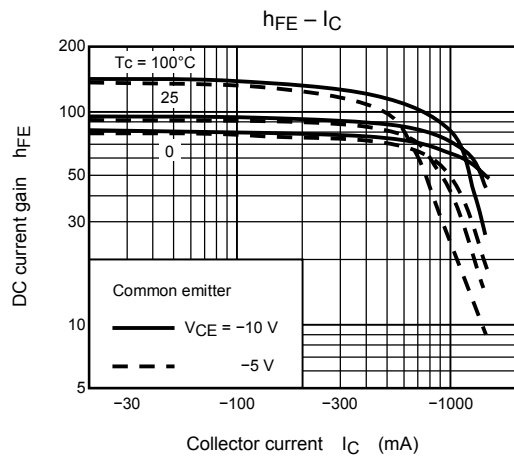
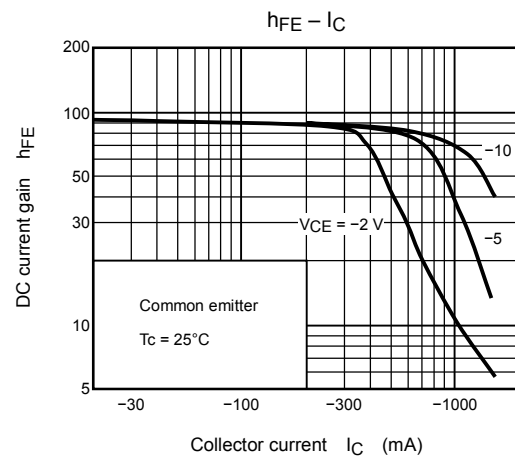
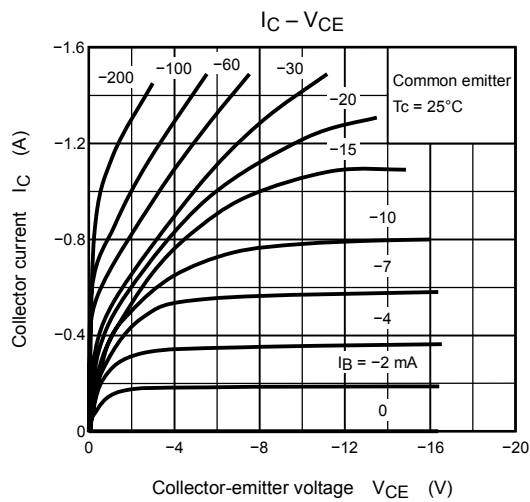
Note: h_{FE} classification R: 60 to 120, O: 100 to 200, Y: 160 to 320

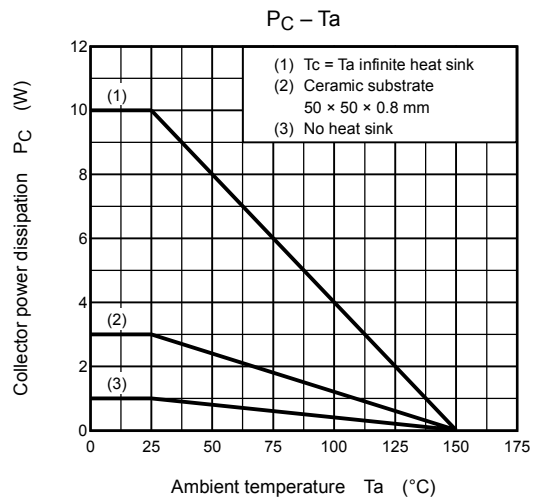
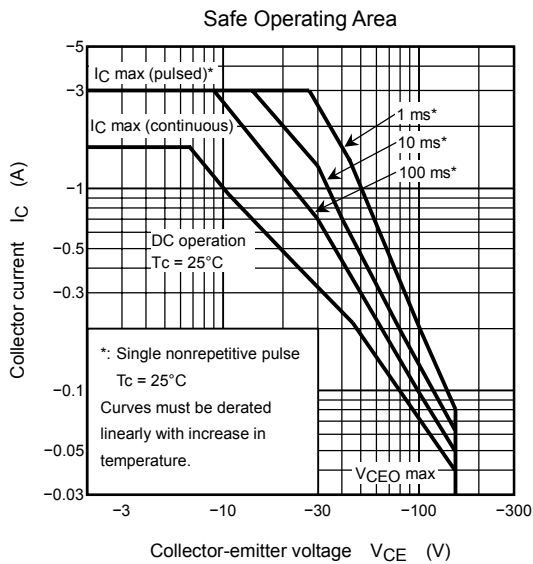
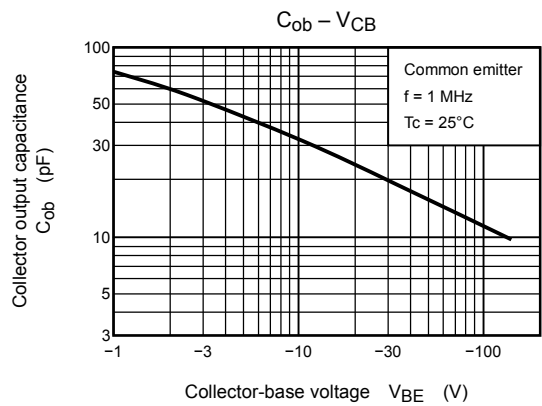
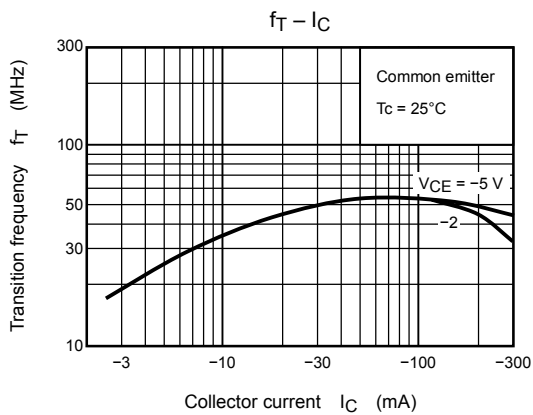
Marking



Explanation of Lot No.







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